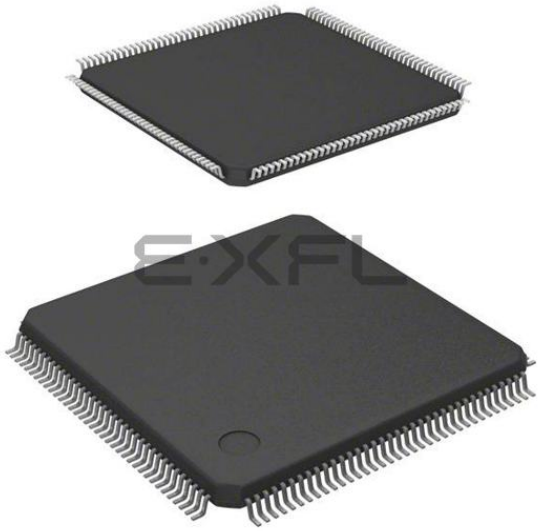

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Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M4
Core Size	32-Bit Single-Core
Speed	72MHz
Connectivity	CANbus, I²C, IrDA, LINbus, SPI, UART/USART, USB
Peripherals	DMA, I²S, POR, PWM, WDT
Number of I/O	115
Program Memory Size	512KB (512K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	80K x 8
Voltage - Supply (Vcc/Vdd)	2V ~ 3.6V
Data Converters	A/D 40x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	144-LQFP
Supplier Device Package	144-LQFP (20x20)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32f303zet6

1 Introduction

This datasheet provides the ordering information and mechanical device characteristics of the STM32F303xD/E microcontrollers.

This STM32F303xD/E datasheet should be read in conjunction with the reference manual of STM32F303xB/C/D/E, STM32F358xC and STM32F328x4/6/8 devices (RM0316) available on STMicroelectronics website at *www.st.com*.

For information on the ARM® Cortex®-M4 core with FPU, refer to the following documents:

- *Cortex® -M4 with FPU Technical Reference Manual*, available from the www.arm.com website
- *STM32F3 and STM32F4 Series Cortex® -M4 programming manual* (PM0214) available on STMicroelectronics website at *www.st.com*.

port analyzer (TPA) device. The TPA is connected to a host computer using a high-speed channel. Real-time instruction and data flow activity can be recorded and then formatted for display on the host computer running debugger software. TPA hardware is commercially available from common development tool vendors. It operates with third party debugger software tools.

Figure 5. STM32F303xD/E LQFP100 pinout

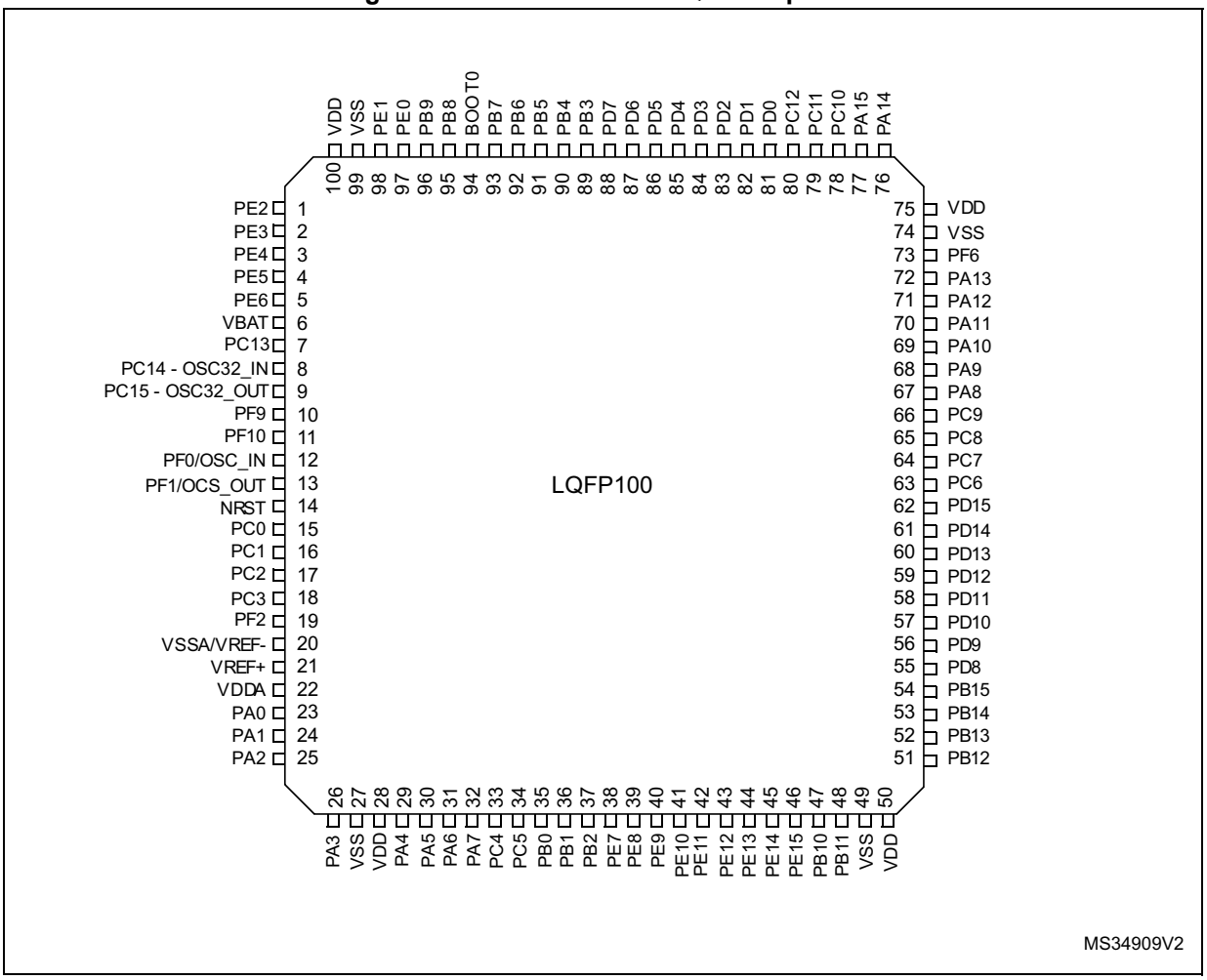


Table 13. STM32F303xD/E pin definitions (continued)

Pin number					Pin name (function after reset)	Pin type	I/O structure	Notes	Alternate functions	Additional functions
LQFP64	LQFP100	UFBGA100	WLCSP100	LQFP144						
-	-	-	-	14	PF4	I/O	TTa	(1)	EVENTOUT, COMP1_OUT, TIM20_CH1N, FMC_A4	ADC1_IN5(3)
-	-	-	-	15	PF5	I/O	FT	(1)	EVENTOUT, TIM20_CH2N, FMC_A5	-
-	-	-	-	16	VSS	S	-	(1)	-	-
-	-	-	-	17	VDD	S	-	(1)	-	-
-	73	C11	C1	18	PF6	I/O	FTf	(1)	EVENTOUT, TIM4_CH4, I2C2_SCL, USART3_RTS, FMC_NIORD	-
-	-	-	-	19	PF7	I/O	FT	(1)	EVENTOUT, TIM20_BKIN, FMC_NREG	-
-	-	-	-	20	PF8	I/O	FT	(1)	EVENTOUT, TIM20_BKIN2, FMC_NIOWR	-
-	10	F2	D10	21	PF9	I/O	FT	(1)	EVENTOUT, TIM20_BKIN, TIM15_CH1, SPI2_SCK, FMC_CD	-
-	11	G2	E10	22	PF10	I/O	FT	(1)	EVENTOUT, TIM20_BKIN2, TIM15_CH2, SPI2_SCK, FMC_INTR	-
5	12	F1	F10	23	PF0-OSC_IN	I	FTf	-	EVENTOUT, I2C2_SDA, SPI2_NSS/I2S2_WS, TIM1_CH3N	OSC_IN
6	13	G1	F9	24	PF1-OSC_OUT	O	FTf	-	EVENTOUT, I2C2_SCL, SPI2_SCK/I2S2_CK	OSC_OUT
7	14	H2	E9	25	NRST	I-O	RST	-	Device reset input/internal reset output (active low)	
8	15	H1	G10	26	PC0	I/O	TTa	-	EVENTOUT, TIM1_CH1	ADC12_IN6, COMP7_INM
9	16	J2	G9	27	PC1	I/O	TTa	-	EVENTOUT, TIM1_CH2	ADC12_IN7, COMP7_INP
10	17	J3	G8	28	PC2	I/O	TTa	-	EVENTOUT, TIM1_CH3, COMP7_OUT	ADC12_IN8

Table 14. STM32F303xD/E alternate function mapping (continued)

Port		AF0	AF1	AF2	AF3	AF4	AF5	AF6	AF7	AF8	AF9	AF10	AF11	AF12	AF13	AF14	AF15
		SYS_AF	TIM2/15/16/17/EVENT	I2C3/TIM1/2/3/4/8/20/15/GPCOMP1	I2C3/TIM8/20/15/GPCOMP7/TSC	I2C1/2/TIM1/8/16/17	SPI1/SPI2/I2S2/SPI3/I2S3/SPI4/UART4/5/TIM8/Infrared	SPI2/I2S2/SPI3/I2S3/TIM1/8/20/Infrared	USART1/2/3/CAN/GPCOMP3/5/6	I2C3/GPCOMP1/2/3/4/5/6	CAN/TIM1/8/15	TIM2/3/4/8/17	TIM1/8	FSMC/TIM1	-	-	EVENT
Port B	PB4	JTRST	TIM16_CH1	TIM3_CH1	TSC_G5_IO2	TIM8_CH2N	SPI1_MISO	SPI3_MISO/I2S3ext_SD	USART2_RX	-	-	TIM17_BKIN	-	-	-	-	EVENTOUT
	PB5	-	TIM16_BKIN	TIM3_CH2	TIM8_CH3N	I2C1_SMBAI	SPI1_MOSI	SPI3_MOSI/I2S3_SD	USART2_CK	I2C3_SDA	-	TIM17_CH1	-	-	-	-	EVENTOUT
	PB6	-	TIM16_CH1N	TIM4_CH1	TSC_G5_IO3	I2C1_SCL	TIM8_CH1	TIM8_ETR	USART1_TX	-	-	TIM8_BKIN2	-	-	-	-	EVENTOUT
	PB7	-	TIM17_CH1N	TIM4_CH2	TSC_G5_IO4	I2C1_SDA	TIM8_BKIN	-	USART1_RX	-	-	TIM3_CH4	-	FMC_NADV	-	-	EVENTOUT
	PB8	-	TIM16_CH1	TIM4_CH3	TSC_SYNC	I2C1_SCL	-	-	USART3_RX	COMP1_OUT	CAN_RX	TIM8_CH2	-	TIM1_BKIN	-	-	EVENTOUT
	PB9	-	TIM17_CH1	TIM4_CH4	-	I2C1_SDA	-	IR-OUT	USART3_TX	COMP2_OUT	CAN_TX	TIM8_CH3	-	-	-	-	EVENTOUT
	PB10	-	TIM2_CH3	-	TSC_SYNC	-	-	-	USART3_TX	-	-	-	-	-	-	-	EVENTOUT
	PB11	-	TIM2_CH4	-	TSC_G6_IO1	-	-	-	USART3_RX	-	-	-	-	-	-	-	EVENTOUT
	PB12	-	-	-	TSC_G6_IO2	I2C2_SMBAL	SPI2_NSS/I2S2_WS	TIM1_BKIN	USART3_CK	-	-	-	-	-	-	-	EVENTOUT
	PB13	-	-	-	TSC_G6_IO3	-	SPI2_SCK/I2S2_CK	TIM1_CH1N	USART3_CTS	-	-	-	-	-	-	-	EVENTOUT

Table 15. Memory map, peripheral register boundary addresses

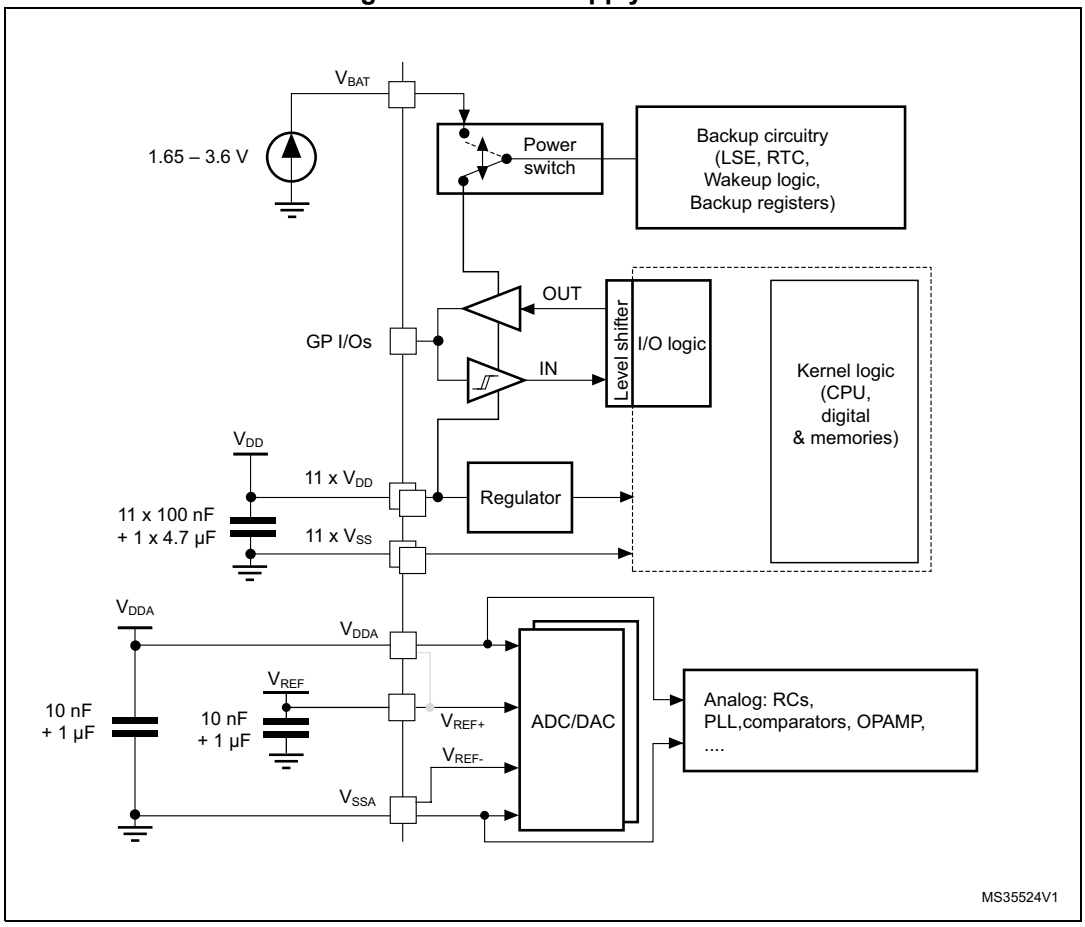
Bus	Boundary address	Size (bytes)	Peripheral
AHB4	0xA000 0000 - 0xA000 0FFF	4 K	FSMC control registers
	0x8000 0000 - 0x9FFF FFFF	512 M	FSMC Banks 3 and 4
	0x6000 0000 - 0x7FFF FFFF	512 M	FSMC Banks 1 and 2
-	0x5000 0800 - 0x5FFF FFFF	384 M	Reserved
AHB3	0x5000 0400 - 0x5000 07FF	1 K	ADC3 - ADC4
	0x5000 0000 - 0x5000 03FF	1 K	ADC1 - ADC2
-	0x4800 2000 - 0x4FFF FFFF	~132 M	Reserved
AHB2	0x4800 1C00 - 0x4800 1FFF	1 K	GPIOH
	0x4800 1800 - 0x4800 1BFF	1 K	GPIOG
	0x4800 1400 - 0x4800 17FF	1 K	GPIOF
	0x4800 1000 - 0x4800 13FF	1 K	GPIOE
	0x4800 0C00 - 0x4800 0FFF	1 K	GPIOD
	0x4800 0800 - 0x4800 0BFF	1 K	GPIOC
	0x4800 0400 - 0x4800 07FF	1 K	GPIOB
	0x4800 0000 - 0x4800 03FF	1 K	GPIOA
-	0x4002 4400 - 0x47FF FFFF	~128 M	Reserved
AHB1	0x4002 4000 - 0x4002 43FF	1 K	TSC
	0x4002 3400 - 0x4002 3FFF	3 K	Reserved
	0x4002 3000 - 0x4002 33FF	1 K	CRC
	0x4002 2400 - 0x4002 2FFF	3 K	Reserved
	0x4002 2000 - 0x4002 23FF	1 K	Flash interface
	0x4002 1400 - 0x4002 1FFF	3 K	Reserved
	0x4002 1000 - 0x4002 13FF	1 K	RCC
	0x4002 0800 - 0x4002 0FFF	2 K	Reserved
	0x4002 0400 - 0x4002 07FF	1 K	DMA2
	0x4002 0000 - 0x4002 03FF	1 K	DMA1

Table 15. Memory map, peripheral register boundary addresses (continued)

Bus	Boundary address	Size (bytes)	Peripheral
APB1	0x4000 7800 - 0x4000 7BFF	1 K	I2C3
	0x4000 7400 - 0x4000 77FF	1 K	DAC
	0x4000 7000 - 0x4000 73FF	1 K	PWR
	0x4000 6800 - 0x4000 6FFF	2 K	Reserved
	0x4000 6400 - 0x4000 67FF	1 K	bxCAN
	0x4000 6000 - 0x4000 63FF	1 K	USB/CAN SRAM
	0x4000 5C00 - 0x4000 5FFF	1 K	USB device FS
	0x4000 5800 - 0x4000 5BFF	1 K	I2C2
	0x4000 5400 - 0x4000 57FF	1 K	I2C1
	0x4000 5000 - 0x4000 53FF	1 K	UART5
	0x4000 4C00 - 0x4000 4FFF	1 K	UART4
	0x4000 4800 - 0x4000 4BFF	1 K	USART3
	0x4000 4400 - 0x4000 47FF	1 K	USART2
	0x4000 4000 - 0x4000 43FF	1 K	I2S3ext
	0x4000 3C00 - 0x4000 3FFF	1 K	SPI3/I2S3
	0x4000 3800 - 0x4000 3BFF	1 K	SPI2/I2S2
	0x4000 3400 - 0x4000 37FF	1 K	I2S2ext
	0x4000 3000 - 0x4000 33FF	1 K	IWDG
	0x4000 2C00 - 0x4000 2FFF	1 K	WWDG
	0x4000 2800 - 0x4000 2BFF	1 K	RTC
	0x4000 1800 - 0x4000 27FF	4 K	Reserved
	0x4000 1400 - 0x4000 17FF	1 K	TIM7
	0x4000 1000 - 0x4000 13FF	1 K	TIM6
	0x4000 0C00 - 0x4000 0FFF	1 K	Reserved
	0x4000 0800 - 0x4000 0BFF	1 K	TIM4
	0x4000 0400 - 0x4000 07FF	1 K	TIM3
	0x4000 0000 - 0x4000 03FF	1 K	TIM2

6.1.6 Power supply scheme

Figure 12. Power supply scheme



1. Dotted lines represent the internal connections on low pin count packages, joining the dedicated supply pins.

Caution: Each power supply pair (V_{DD}/V_{SS}, V_{DDA}/V_{SSA} etc.) must be decoupled with filtering ceramic capacitors as shown above. These capacitors must be placed as close as possible to, or below the appropriate pins on the underside of the PCB to ensure the good functionality of the device.

6.3.2 Operating conditions at power-up / power-down

The parameters given in *Table 20* are derived from tests performed under the ambient temperature condition summarized in *Table 19*.

Table 20. Operating conditions at power-up / power-down

Symbol	Parameter	Conditions	Min	Max	Unit
t_{VDD}	V_{DD} rise time rate	-	0	∞	µs/V
	V_{DD} fall time rate		20	∞	
t_{VDDA}	V_{DDA} rise time rate	-	0	∞	
	V_{DDA} fall time rate		20	∞	

6.3.3 Embedded reset and power control block characteristics

The parameters given in *Table 21* are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in *Table 19*.

Table 21. Embedded reset and power control block characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
$V_{POR/PDR}$(1)	Power on/power down reset threshold	Falling edge	1.8(2)	1.88	1.96	V
		Rising edge	1.84	1.92	2.0	V
$V_{PDRhyst}$(1)	PDR hysteresis	-	-	40	-	mV

1. The PDR detector monitors V_{DD} and also V_{DDA} (if kept enabled in the option bytes). The POR detector monitors only V_{DD}.
2. The product behavior is guaranteed by design down to the minimum $V_{POR/PDR}$ value.

Table 22. Programmable voltage detector characteristics

Symbol	Parameter	Conditions	Min(1)	Typ	Max(1)	Unit
V_{PVD0}	PVD threshold 0	Rising edge	2.1	2.18	2.26	V
		Falling edge	2	2.08	2.16	
V_{PVD1}	PVD threshold 1	Rising edge	2.19	2.28	2.37	
		Falling edge	2.09	2.18	2.27	
V_{PVD2}	PVD threshold 2	Rising edge	2.28	2.38	2.48	
		Falling edge	2.18	2.28	2.38	
V_{PVD3}	PVD threshold 3	Rising edge	2.38	2.48	2.58	
		Falling edge	2.28	2.38	2.48	
V_{PVD4}	PVD threshold 4	Rising edge	2.47	2.58	2.69	
		Falling edge	2.37	2.48	2.59	
V_{PVD5}	PVD threshold 5	Rising edge	2.57	2.68	2.79	
		Falling edge	2.47	2.58	2.69	

6.3.7 External clock source characteristics

High-speed external user clock generated from an external source

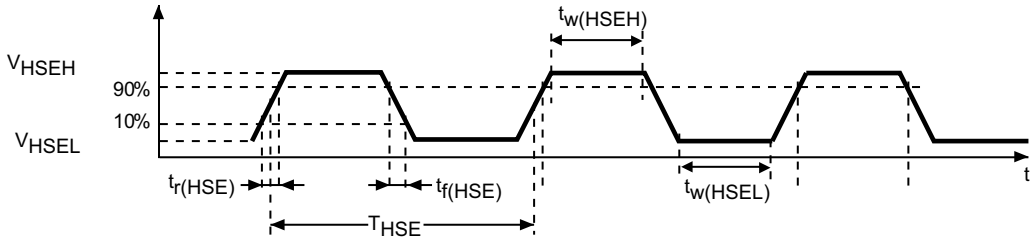
In bypass mode the HSE oscillator is switched off and the input pin is a standard GPIO. The external clock signal has to respect the I/O characteristics in *Section 6.3.15*. However, the recommended clock input waveform is shown in *Figure 15*.

Table 36. High-speed external user clock characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{HSE_ext}	User external clock source frequency(1)	-	1	8	32	MHz
V_{HSEH}	OSC_IN input pin high level voltage		$0.7V_{DD}$	-	V_{DD}	V
V_{HSEL}	OSC_IN input pin low level voltage		V_{SS}	-	$0.3V_{DD}$	
$t_{w(HSEH)}$ $t_{w(HSEL)}$	OSC_IN high or low time(1)		15	-	-	ns
$t_{r(HSE)}$ $t_{f(HSE)}$	OSC_IN rise or fall time(1)		-	-	20	

1. Guaranteed by design, not tested in production.

Figure 15. High-speed external clock source AC timing diagram



Low-speed external user clock generated from an external source

In bypass mode the LSE oscillator is switched off and the input pin is a standard GPIO. The external clock signal has to respect the I/O characteristics in *Section 6.3.15*. However, the recommended clock input waveform is shown in *Figure 16*.

High-speed external clock generated from a crystal/ceramic resonator

The high-speed external (HSE) clock can be supplied with a 4 to 32 MHz crystal/ceramic resonator oscillator. All the information given in this paragraph are based on design simulation results obtained with typical external components specified in *Table 38*. In the application, the resonator and the load capacitors have to be placed as close as possible to the oscillator pins to minimize output distortion and startup stabilization time. Refer to the crystal resonator manufacturer for more details on the resonator characteristics (frequency, package, accuracy).

Table 38. HSE oscillator characteristics

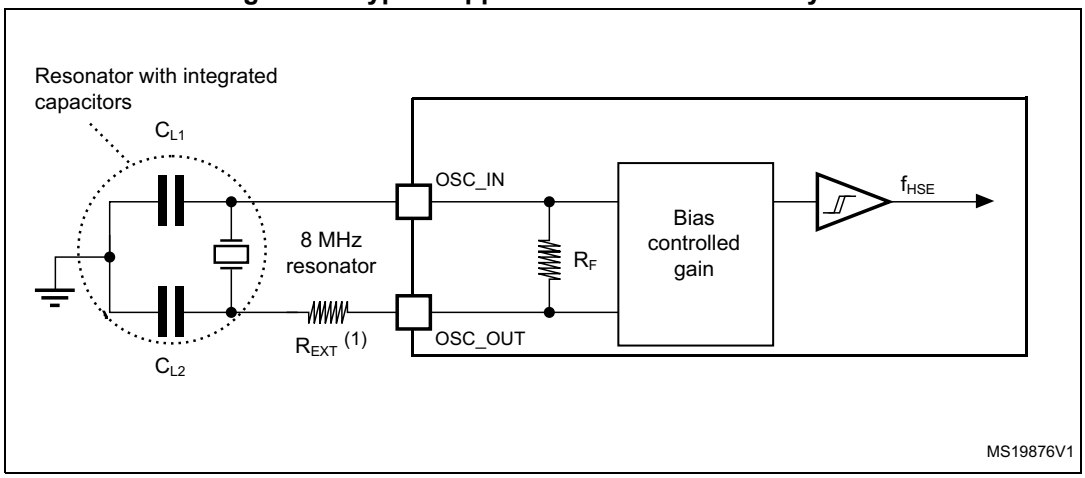
Symbol	Parameter	Conditions(1)	Min(2)	Typ	Max(2)	Unit
f_{OSC_IN}	Oscillator frequency	-	4	8	32	MHz
R_F	Feedback resistor	-	-	200	-	kΩ
I_{DD}	HSE current consumption	During startup(3)	-	-	8.5	mA
		V_{DD}= 3.3 V, Rm= 30Ω, CL=10 pF@8 MHz	-	0.4	-	
		V_{DD}= 3.3 V, Rm= 45Ω, CL=10 pF@8 MHz	-	0.5	-	
		V_{DD}= 3.3 V, Rm= 30Ω, CL=5 pF@32 MHz	-	0.8	-	
		V_{DD}= 3.3 V, Rm= 30Ω, CL=10 pF@32 MHz	-	1	-	
		V_{DD}= 3.3 V, Rm= 30Ω, CL=20 pF@32 MHz	-	1.5	-	
g_m	Oscillator transconductance	Startup	10	-	-	mA/V
$t_{SU(HSE)}$(4)	Startup time	V_{DD} is stabilized	-	2	-	ms

1. Resonator characteristics given by the crystal/ceramic resonator manufacturer.
2. Guaranteed by design, not tested in production.
3. This consumption level occurs during the first 2/3 of the $t_{SU(HSE)}$ startup time.
4. $t_{SU(HSE)}$ is the startup time measured from the moment it is enabled (by software) to a stabilized 8 MHz oscillation is reached. This value is measured for a standard crystal resonator and it can vary significantly with the crystal manufacturer.

For C_{L1} and C_{L2}, it is recommended to use high-quality external ceramic capacitors in the 5 pF to 25 pF range (Typ.), designed for high-frequency applications, and selected to match the requirements of the crystal or resonator (see *Figure 17*). C_{L1} and C_{L2} are usually the same size. The crystal manufacturer typically specifies a load capacitance which is the series combination of C_{L1} and C_{L2}. PCB and MCU pin capacitance must be included (10 pF can be used as a rough estimate of the combined pin and board capacitance) when sizing C_{L1} and C_{L2}.

Note: For information on selecting the crystal, refer to the application note AN2867 "Oscillator design guide for ST microcontrollers" available from the ST website www.st.com.

Figure 17. Typical application with an 8 MHz crystal



1. R_{EXT} value depends on the crystal characteristics.

Low-speed external clock generated from a crystal/ceramic resonator

The low-speed external (LSE) clock can be supplied with a 32.768 kHz crystal/ceramic resonator oscillator. All the information given in this paragraph are based on design simulation results obtained with typical external components specified in *Table 39*. In the application, the resonator and the load capacitors have to be placed as close as possible to the oscillator pins to minimize output distortion and startup stabilization time. Refer to the crystal resonator manufacturer for more details on the resonator characteristics (frequency, package, accuracy).

Table 39. LSE oscillator characteristics (f_{LSE} = 32.768 kHz)

Symbol	Parameter	Conditions(1)	Min(2)	Typ	Max(2)	Unit
I_{DD}	LSE current consumption	LSEDRV[1:0]=00 lower driving capability	-	0.5	0.9	µA
		LSEDRV[1:0]=01 medium low driving capability	-	-	1	
		LSEDRV[1:0]=10 medium high driving capability	-	-	1.3	
		LSEDRV[1:0]=11 higher driving capability	-	-	1.6	
g_m	Oscillator transconductance	LSEDRV[1:0]=00 lower driving capability	5	-	-	µA/V
		LSEDRV[1:0]=01 medium low driving capability	8	-	-	
		LSEDRV[1:0]=10 medium high driving capability	15	-	-	
		LSEDRV[1:0]=11 higher driving capability	25	-	-	
$t_{SU(LSE)}$(3)	Startup time	V_{DD} is stabilized	-	2	-	s

1. Refer to the note and caution paragraphs below the table, and to the application note AN2867 “Oscillator design guide for ST microcontrollers”.
2. Guaranteed by design, not tested in production.
3. $t_{SU(LSE)}$ is the startup time measured from the moment it is enabled (by software) to a stabilized 32.768 kHz oscillation is reached. This value is measured for a standard crystal and it can vary significantly with the crystal manufacturer.

Static latch-up

Two complementary static tests are required on six parts to assess the latch-up performance:

- A supply overvoltage is applied to each power supply pin
- A current injection is applied to each input, output and configurable I/O pin

These tests are compliant with EIA/JESD 78A IC latch-up standard.

Table 64. Electrical sensitivities

Symbol	Parameter	Conditions	Class
LU	Static latch-up class	T_A = +105 °C conforming to JESD78A	II Level A

6.3.14 I/O current injection characteristics

As a general rule, current injection to the I/O pins, due to external voltage below V_{SS} or above V_{DD} (for standard, 3 V-capable I/O pins) should be avoided during normal product operation. However, to give an indication of the robustness of the microcontroller in cases when abnormal injection accidentally happens, susceptibility tests are performed on a sample basis during device characterization.

Functional susceptibility to I/O current injection

While a simple application is executed on the device, the device is stressed by injecting current into the I/O pins programmed in floating input mode. While current is injected into the I/O pin, one at a time, the device is checked for functional failures.

The failure is indicated by an out of range parameter: ADC error above a certain limit (higher than 5 LSB TUE), out of conventional limits of induced leakage current on adjacent pins (out of –5 µA/+0 µA range), or other functional failure (for example reset occurrence or oscillator frequency deviation).

The test results are given in *Table 65*.

Table 65. I/O current injection susceptibility

Symbol	Description	Functional susceptibility		Unit
		Negative injection	Positive injection	
I_{INJ}	Injected current on BOOT0	-0	NA	mA
	Injected current on PF3, PC1, PC2, PA1, PA2, PA3, PA4, PA5, PA6, PA7, PB0, PB1, PE8, PE9, PE10, PE11, PE12, PE13, PE14, PE15, PB13, PB14, PB15, PD8, PD9, PD10, PD11, PD12, PD13, PD14 pins with induced leakage current on adjacent pins less than -50 µA or more than +400 µA	-5	+5	
	Injected current on PF2, PF4, PC0, PC1, PC2, PC3, PA0, PA1, PA2, PA3, PA4, PA5, PA6, PA7, PC4, PC5, PB2, PB11 with induced leakage current on other pins from this group less than -50 µA or more than +400 µA	-5	+5	

Output driving current

The GPIOs (general purpose input/outputs) can sink or source up to +/-8 mA, and sink or source up to +/- 20 mA (with a relaxed V_{OL}/V_{OH}).

In the user application, the number of I/O pins which can drive current must be limited to respect the absolute maximum rating specified in *Section 6.2*:

- The sum of the currents sourced by all the I/Os on $V_{DD,}$ plus the maximum Run consumption of the MCU sourced on $V_{DD,}$ cannot exceed the absolute maximum rating ΣI_{VDD} (see *Table 17*).
- The sum of the currents sunk by all the I/Os on V_{SS} plus the maximum Run consumption of the MCU sunk on V_{SS} cannot exceed the absolute maximum rating ΣI_{VSS} (see *Table 17*).

Output voltage levels

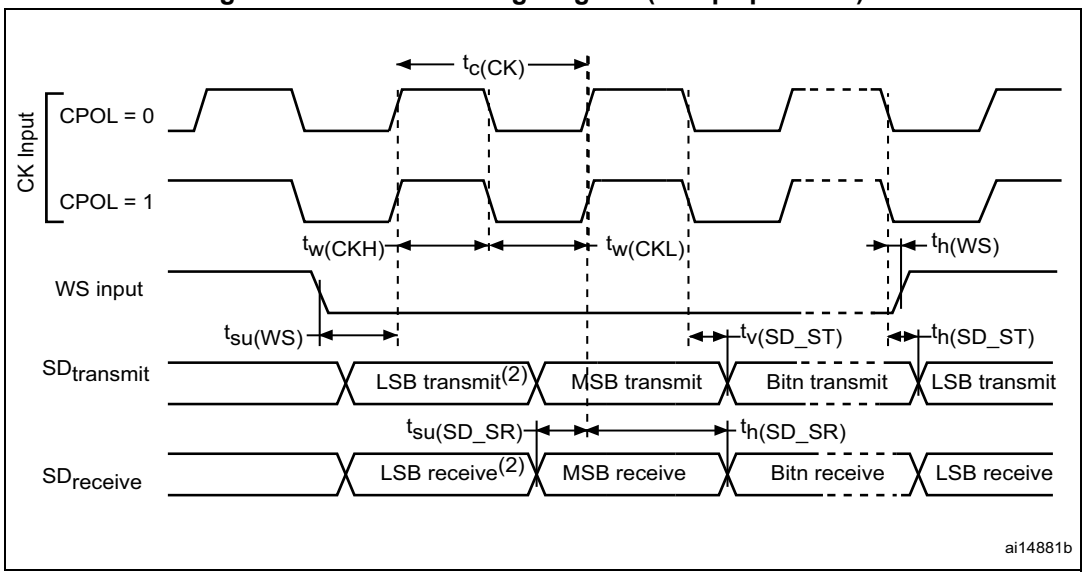
Unless otherwise specified, the parameters given in *Table 67* are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in *Table 19*. All I/Os (FT, TTa and TC unless otherwise specified) are CMOS and TTL compliant.

Table 67. Output voltage characteristics

Symbol	Parameter	Conditions	Min	Max	Unit
V_{OL} (1)	Output low level voltage for an I/O pin	CMOS port(2) I_{IO} = +48 mA 2.7 V < V_{DD} < 3.6 V	-	0.4	V
V_{OH} (3)	Output high level voltage for an I/O pin		V_{DD}–0.4	-	
V_{OL} (1)	Output low level voltage for an I/O pin	TTL port(2) I_{IO} = +8 mA 2.7 V < V_{DD} < 3.6 V	-	0.4	
V_{OH} (3)	Output high level voltage for an I/O pin		2.4	-	
V_{OL} (1)(4)	Output low level voltage for an I/O pin	I_{IO} = +20 mA 2.7 V < V_{DD} < 3.6 V	-	1.3	
V_{OH} (3)(4)	Output high level voltage for an I/O pin		V_{DD}–1.3	-	
V_{OL} (1)(4)	Output low level voltage for an I/O pin	I_{IO} = +6 mA 2 V < V_{DD} < 2.7 V	-	0.4	
V_{OH} (3)(4)	Output high level voltage for an I/O pin		V_{DD}–0.4	-	
V_{OLFM+} (4)(4)	Output low level voltage for an FTf I/O pin in FM+ mode	I_{IO} = +20 mA 2.7 V < V_{DD} < 3.6 V	-	0.4	

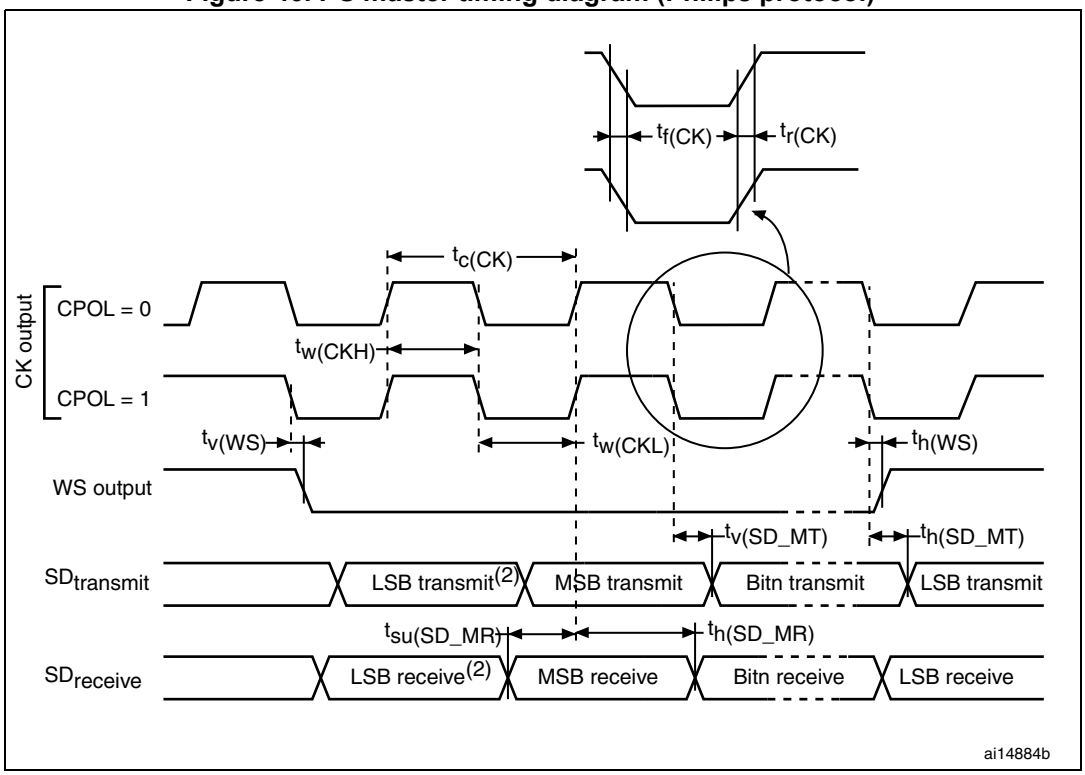
1. The I_{IO} current sunk by the device must always respect the absolute maximum rating specified in *Table 17* and the sum of I_{IO} (I/O ports and control pins) must not exceed $\Sigma I_{IO(PIN)}$.
2. TTL and CMOS outputs are compatible with JEDEC standards JESD36 and JESD52.
3. The I_{IO} current sourced by the device must always respect the absolute maximum rating specified in *Table 17* and the sum of I_{IO} (I/O ports and control pins) must not exceed $\Sigma I_{IO(PIN)}$.
4. Data based on design simulation.

Figure 45. I²S slave timing diagram (Philips protocol)(1)



1. Measurement points are done at $0.5V_{DD}$ and with external C_L=30 pF.
2. LSB transmit/receive of the previously transmitted byte. No LSB transmit/receive is sent before the first byte.

Figure 46. I²S master timing diagram (Philips protocol)(1)



1. Measurement points are done at $0.5V_{DD}$ and with external C_L=30 pF.
2. LSB transmit/receive of the previously transmitted byte. No LSB transmit/receive is sent before the first byte.

USB characteristics

Table 76. USB startup time

Symbol	Parameter	Max	Unit
$t_{STARTUP}$(1)	USB transceiver startup time	1	µs

1. Guaranteed by design, not tested in production.

Table 77. USB DC electrical characteristics

Symbol	Parameter	Conditions	Min.(1)	Max.(1)	Unit
Input levels					
V_{DD}	USB operating voltage(2)	-	3.0(3)	3.6	V
V_{DI}(4)	Differential input sensitivity	I(USB_DP, USB_DM)	0.2	-	V
V_{CM}(4)	Differential common mode range	Includes V_{DI} range	0.8	2.5	
V_{SE}(4)	Single ended receiver threshold	-	1.3	2.0	
Output levels					
V_{OL}	Static output level low	R_L of 1.5 kΩ to 3.6 V(5)	-	0.3	V
V_{OH}	Static output level high	R_L of 15 kΩ to V_{SS}(5)	2.8	3.6	

1. All the voltages are measured from the local ground potential.
2. To be compliant with the USB 2.0 full-speed electrical specification, the USB_DP (D+) pin should be pulled up with a 1.5 kΩ resistor to a 3.0-to-3.6 V voltage range.
3. The STM32F303xD/E USB functionality is ensured down to 2.7 V but not the full USB electrical characteristics which are degraded in the 2.7-to-3.0 V V_{DD} voltage range.
4. Guaranteed by design, not tested in production.
5. R_L is the load connected on the USB drivers.

Figure 47. USB timings: definition of data signal rise and fall time

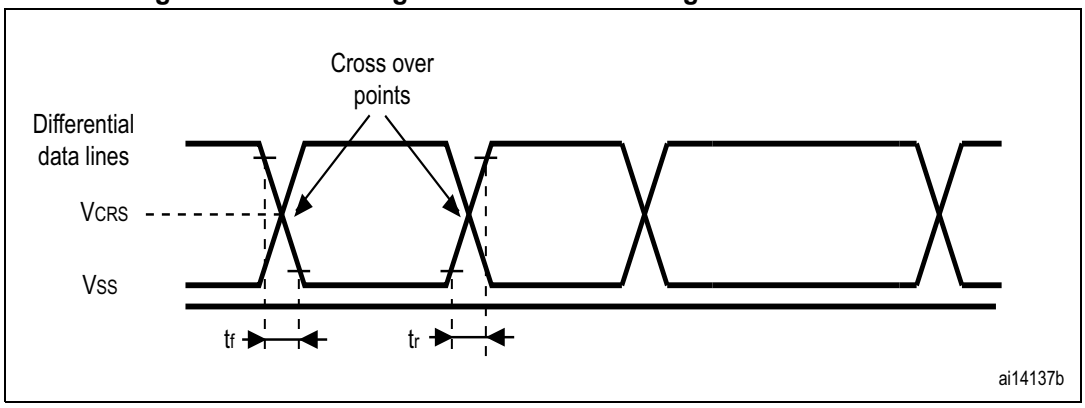


Table 78. USB: full-speed electrical characteristics(1)

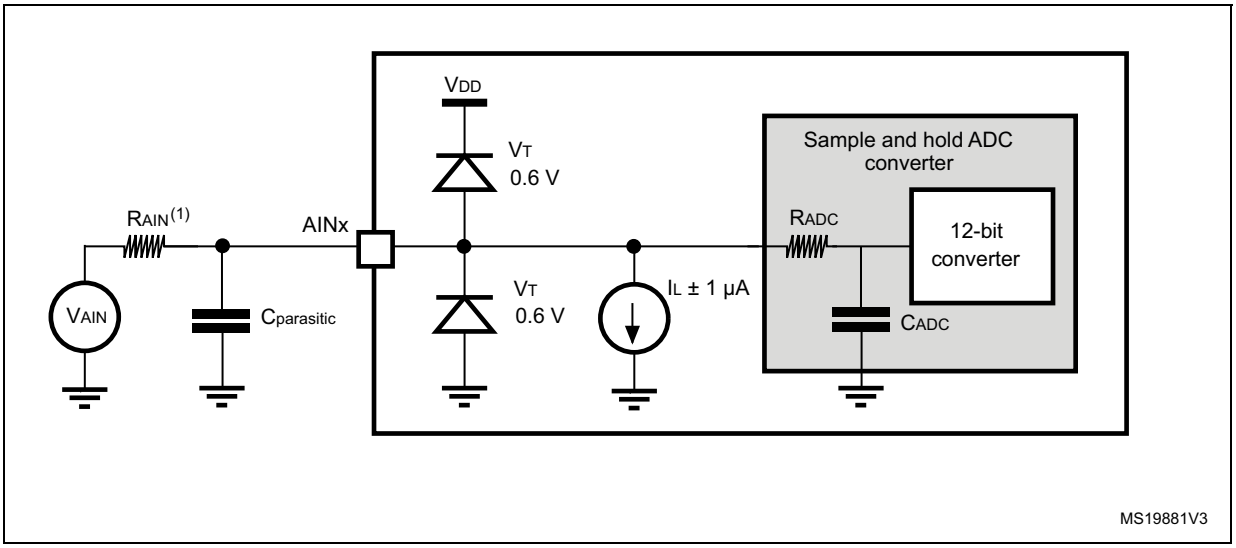
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Driver characteristics						
t_r	Rise time(2)	C_L = 50 pF	4	-	20	ns
t_f	Fall time(2)	C_L = 50 pF	4	-	20	ns

Table 82. ADC accuracy, 100-pin/144-pin packages(1)(2)(3) (continued)

Symbol	Parameter	Conditions			Min (4)	Max(4)	Unit
EL	Integral linearity error	ADC clock freq. ≤ 72 MHz, Sampling freq. ≤ 5 Msps, 2.0 V≤ V_{DDA}, V_{REF+} ≤ 3.6 V 100-pin/144-pin package	Single Ended	Fast channel 5.1 Ms	-	±2	LSB
				Slow channel 4.8 Ms	-	±3	
			Differential	Fast channel 5.1 Ms	-	±2	
				Slow channel 4.8 Ms	-	±2	
ENOB (5)	Effective number of bits		Single Ended	Fast channel 5.1 Ms	10.4	-	bits
				Slow channel 4.8 Ms	10.2	-	
			Differential	Fast channel 5.1 Ms	10.8	-	
				Slow channel 4.8 Ms	10.8	-	
SINAD (5)	Signal-to-noise and distortion ratio		Single Ended	Fast channel 5.1 Ms	64	-	dB
				Slow channel 4.8 Ms	63	-	
			Differential	Fast channel 5.1 Ms	67	-	
				Slow channel 4.8 Ms	67	-	
SNR(5)	Signal-to-noise ratio		Single Ended	Fast channel 5.1 Ms	64	-	
				Slow channel 4.8 Ms	64	-	
			Differential	Fast channel 5.1 Ms	67	-	
				Slow channel 4.8 Ms	67	-	
THD(5)	Total harmonic distortion		Single Ended	Fast channel 5.1 Ms	-	74	
				Slow channel 4.8 Ms	-	-74	
			Differential	Fast channel 5.1 Ms	-	-78	
				Slow channel 4.8 Ms	-	-76	

1. ADC DC accuracy values are measured after internal calibration.
2. ADC accuracy vs. negative Injection Current: Injecting negative current on any analog input pins should be avoided as this significantly reduces the accuracy of the conversion being performed on another analog input. It is recommended to add a Schottky diode (pin to ground) to analog pins which may potentially inject negative current.
   Any positive injection current within the limits specified for $I_{INJ(PIN)}$ and $\Sigma I_{INJ(PIN)}$ in *Section 6.3.15* does not affect the ADC accuracy.
3. Better performance may be achieved in restricted V_{DDA}, frequency and temperature ranges.
4. Data based on characterization results, not tested in production.
5. Value measured with a -0.5 dB full scale 50 kHz sine wave input signal.

Figure 51. Typical connection diagram using the ADC



1. Refer to *Table 79* for the values of R_{AIN}.
2. $C_{parasitic}$ represents the capacitance of the PCB (dependent on soldering and PCB layout quality) plus the pad capacitance (roughly 7 pF). A high $C_{parasitic}$ value downgrades conversion accuracy. To remedy this, f_{ADC} should be reduced.

General PCB design guidelines

Power supply decoupling should be performed as shown in *Figure 12*. The 10 nF capacitor should be ceramic (good quality) and it should be placed as close as possible to the chip.

6.3.20 DAC electrical specifications

Table 86. DAC characteristics

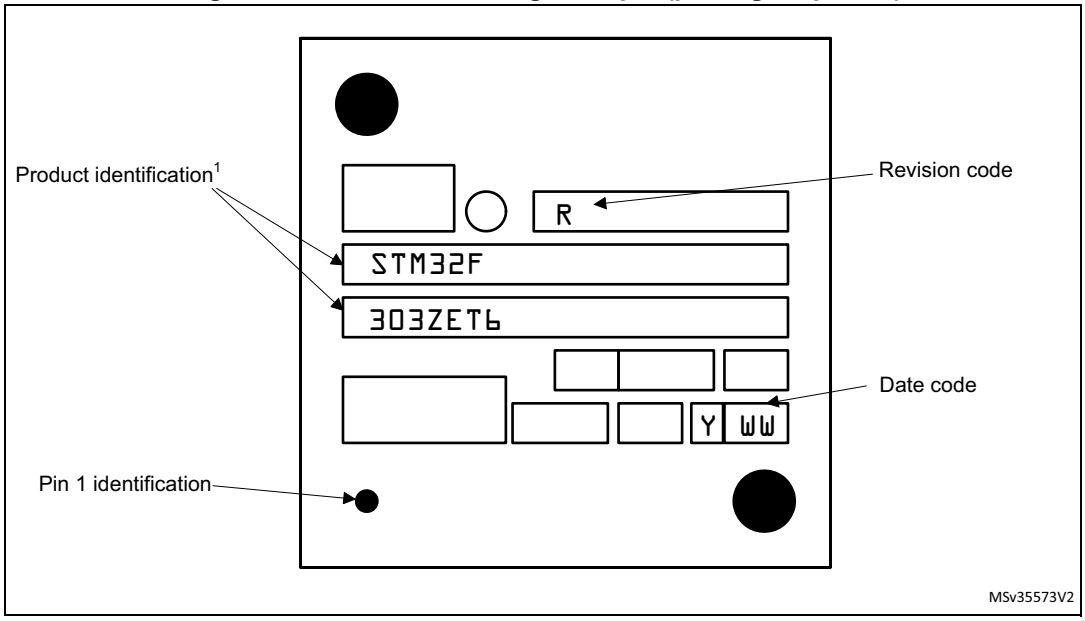
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DDA}	Analog supply voltage	-	2.4	-	3.6	V
R_{LOAD}(1)	Resistive load	DAC output buffer ON	5	-	-	kΩ
R_L	Resistive load	Dac output buffer ON: connected to V_{SSA}	5	-	-	kΩ
		Dac output buffer ON: connected to V_{DDA}	25	-	-	kΩ
R_O(1)	Output impedance	DAC output buffer OFF	-	-	15	kΩ
C_{LOAD}(1)	Capacitive load	DAC output buffer ON	-	-	50	pF
V_{DAC_OUT} (1)	Voltage on DAC_OUT output	Corresponds to 12-bit input code (0x0E0) to (0xF1C) at V_{DDA} = 3.6 V and (0x155) and (0xEAB) at V_{DDA} = 2.4 V DAC output buffer ON.	0.2	-	V_{DDA} – 0.2	V
		DAC output buffer OFF	-	0.5	V_{DDA} - 1LSB	mV

Device marking for LQFP144

The following figure gives an example of topside marking orientation versus pin 1 identifier location.

Other optional marking or inset/upset marks, which identify the parts throughout supply chain operations, are not indicated below.

Figure 56. LQFP144 marking example (package top view)

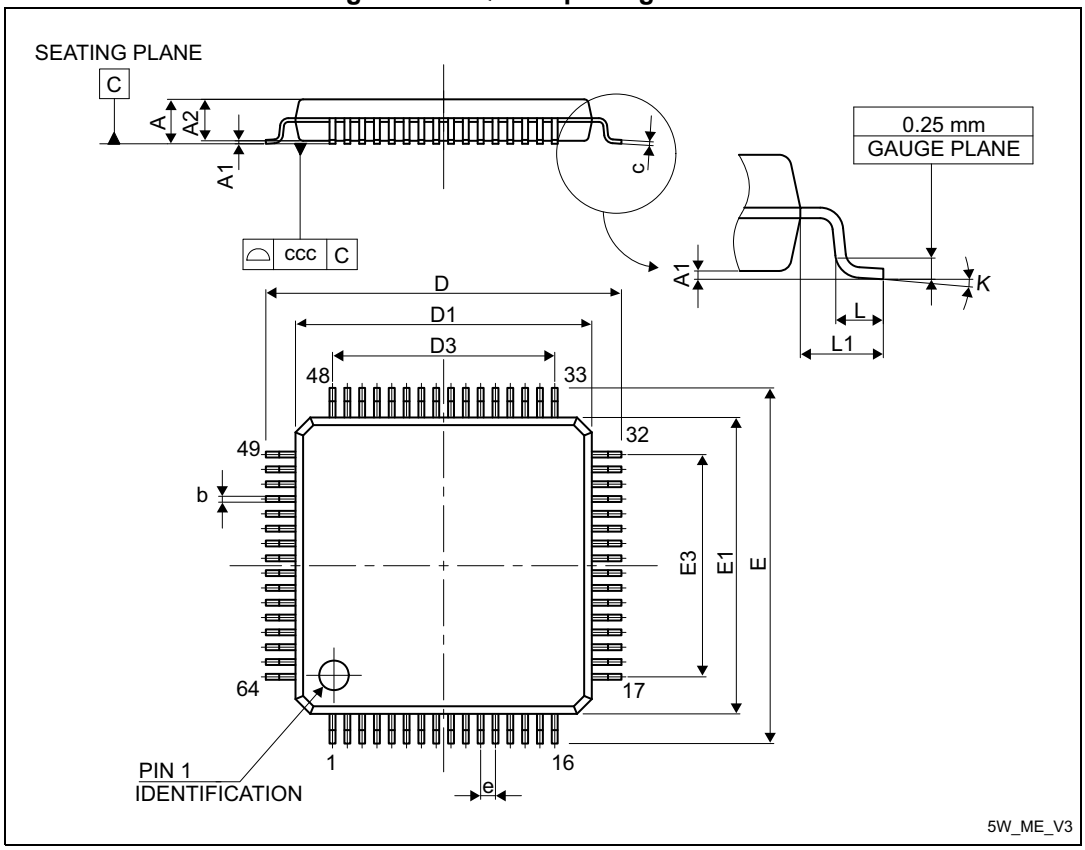


1. Parts marked as “ES”, “E” or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering samples to run qualification activity.

7.6 LQFP64 package information

LQFP64 is a 64-pin, 10 x 10 mm low-profile quad flat package.

Figure 66. LQFP64 package outline



1. Drawing is not to scale.

Table 98. LQFP64 package mechanical data

Symbol	millimeters			inches[1]		
	Min	Typ	Max	Min	Typ	Max
A	-	-	1.600	-	-	0.0630
A1	0.050	-	0.150	0.0020	-	0.0059
A2	1.350	1.400	1.450	0.0531	0.0551	0.0571
b	0.170	0.220	0.270	0.0067	0.0087	0.0106
c	0.090	-	0.200	0.0035	-	0.0079
D	-	12.000	-	-	0.4724	-
D1	-	10.000	-	-	0.3937	-
D3	-	7.500	-	-	0.2953	-
E	-	12.000	-	-	0.4724	-
E1	-	10.000	-	-	0.3937	-